

Abstract of the Disclosure

A semiconductor device includes a conductive region and line, and a contact plug electrically connecting the line and the region. The line is connected to the region via sidewalls of the plug, and the region is connected to the line via the bottom of the plug. The cross-sectional area of the plug decreases in a direction from an upper to lower portion thereof. In a first method of fabricating a semiconductor device having a self-aligned contact, the plug is formed after the line is formed in an interlayer dielectric layer. Portions of the dielectric layer and line are etched to form a contact hole in which the plug is formed. In a second method, a line having a gap therein is formed in an interlayer dielectric layer. Portions of the dielectric layer, including the gap in the line, are etched to form the contact hole.